

US010374044B2

(12) United States Patent Iijima et al.

(54) SEMICONDUCTOR DEVICE, INVERTER CIRCUIT, DRIVING DEVICE, VEHICLE, AND ELEVATOR

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(*) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35

U.S.C. 154(b) by 0 days.

(21) Appl. No.: 16/059,235

(22) Filed: Aug. 9, 2018

(65) **Prior Publication Data**

US 2019/0198619 A1 Jun. 27, 2019

(30) Foreign Application Priority Data

Dec. 21, 2017 (JP) 2017-244584

(51) **Int. Cl. H01L 29/16** (2006.01) **H01L 21/02** (2006.01)

(Continued)

(52) **U.S. CI.**CPC *H01L 29/1608* (2013.01); *H01L 21/02529* (2013.01); *H01L 21/045* (2013.01); (Continued)

(58) Field of Classification Search

CPC H01L 29/1608; H01L 29/66068; H01L 29/086; H01L 29/7813; H01L 29/66734; (Continued)

(10) Patent No.: US 10,374,044 B2

(45) **Date of Patent:** Aug. 6, 2019

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(57) ABSTRACT

A semiconductor device of an embodiment includes a silicon carbide layer having a first plane and a second plane; a trench having a first side face, a second side face, and a bottom face; a first silicon carbide region of a first conductivity type; a second silicon carbide region and a third silicon carbide region of a second conductivity type, the third silicon carbide region and the second silicon carbide region sandwiching the trench; a sixth silicon carbide region of a second conductivity type in contact with the second side face and the bottom face; and a gate electrode in the trench. The first side face has a first region having a first inclination angle. The off angle of the first region with respect to a {0-33-8} face is no more than 2 degrees. A second inclination angle of the second side face is larger the first inclination angle.

10 Claims, 22 Drawing Sheets

